

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	861	(wafer or semiconductor or substrate) and dielectric and (open or via or hole or trench) and scribe and die and (metal or conduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S2	872	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S3	414	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S4	336	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4) and stress and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S5	272	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4) and stress and plurality and expos\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S6	206	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4) and stress and plurality and expos\$3 and region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S7	27	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct\$4) and stress and plurality and expos\$3 and region and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:19

## EAST Search History

S8	6	die and "scribe line" and (wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct\$4) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:24
S9	43	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct\$4) and pit and "scribe line"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:02
S10	6	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct\$4) and pit and "scribe line" and die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:59
S11	194	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat\$4) and (via or hole or trench) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph\$8 and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:05
S12	20	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat\$4) and (via or hole or trench or open\$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph\$8 and etch and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:06
S13	0	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat\$4) and (via or hole or trench or open\$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph\$8 and etch and (scribe near4 line) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:13
S14	27	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat\$4) and (via or hole or trench or open\$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph\$8 and etch and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:15

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S15	15	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat\$4) and (via or hole or trench or open\$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph\$8 and etch and pit and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:19
S16	33326	(stress near4 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S17	787	((stress near4 (wafer or semiconductor or substrate)) near4 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S18	480	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat\$4) and (open\$3 or via or hole or trench or groove) and pit\$2 and (photolithographic\$4 or etch\$4) and plug and (metal or conduct\$4 or polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:24
S19	70	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat\$4) and (open\$3 or via or hole or trench or groove) and pit\$2 and (photolithographic\$4 or etch\$4) and plug and (metal or conduct\$4 or polysilicon) and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:25
S20	63	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat\$4) and (open\$3 or via or hole or trench or groove) and pit\$2 and (photolithographic\$4 or etch\$4) and plug and (metal or conduct\$4 or polysilicon) and (scribe near line) and (tungsten or copper)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:25